

CLAIMS:

1. Support plate for supporting at least one component, in particular an IC or other semiconductor component, more particularly a wafer, on a top face of said support plate, characterized in that the top face is at least partially roughened.
- 5 2. Support plate according to claim 1, wherein the at least partially roughened top face of the support plate has a roughness Ra in the range of 0.10 - 3.0 μm , preferably in the range of 0.20 - 2.0 μm , even more preferably in the range of 0.25 - 1.0 μm , most preferably about 0.3 μm .
- 10 3. Support plate according to claim 1, wherein the top face comprises a groove or a pattern of grooves, the at least one groove preferably preventing or at least minimizing the formation of an 'air cushion' between the top face and the at least one component.
- 15 4. Support plate according to claim 3, wherein the at least one groove has a depth of about 0.20 mm.
5. Support plate according to claim 1, wherein the top face comprises at least one recess for at least partially receiving the at least one component.
- 20 6. Support plate according to claim 1, wherein the support plate is made from a non-corrosive, non-contaminating material.
7. Support plate according to claim 1, wherein the support plate is made from a material selected from a group of materials comprising glass, granite and ceramic and a
25 combination thereof, more preferably glass, most preferably transparent glass.
8. Use of the support plate according to claim 1 as a slide for spectroscopic analysis.

9. Use according to claim 8, wherein the top face of the slide has a roughness such that, during spectroscopic analysis, no interference caused by the roughness of the top face of the slide occurs.

5 10. Method for the preparation of a support plate for supporting at least one component, in particular an IC or other semiconductor component, more particularly a wafer, on a top face of said support plate, characterized by the steps of:

- forming the support plate; and

10 - roughening the top face of the formed support plate at least partially using powder blasting such that the at least partially roughened top surface of the support plate has a roughness Ra in the range of 0.10 - 3.0 μm , preferably in the range of 0.20 - 2.0 μm , even more preferably in the range of 0.25 - 1.0 μm , most preferably about 0.3 μm .

11. Packaging unit for packaging at least one component, in particular an IC or
15 other semiconductor component, more particularly a wafer, said packaging unit comprising a support plate according to claim 1.

12. Packaging unit according to claim 11, wherein the packaging unit further
20 comprises a cover plate having a bottom face facing the top face of the support plate, the bottom face of the cover plate being at least partially roughened and being releasably connectable to the top face of the support plate.

13. Packaging unit according to claim 10, wherein the top face of the support plate
25 and the bottom face of the cover plate each comprise at least one recess, which recesses are designed to at least partially receive the at least one component to be packaged.

14. Use of the packaging unit according to claim 11 for storage of components, in particular ICs or other semiconductor components, more particularly wafers.

30 15. Use of a non-corrosive, non-contaminating material, preferably selected from the group comprising glass, granite and ceramic and a combination thereof, more preferably glass, most preferably transparent glass, in the packaging of ICs or other semiconductor components, in particular wafers.